

MDDG10R160D

100V P-Channel Enhancement Mode MOSFET

1. Description

This P-Channel MOSFET is produced using MDD's advanced Power Trench technology. This process has been optimized to minimize on-state resistance and yet maintain superior switching performance with best in class soft body diode.

2. Features

- Max $R_{DS(on)}$ = 175m Ω at V_{GS} = -10 V, I_D = -12 A
- Extremely Low Reverse Recovery Charge, Q_g
- 100% UIS Tested
- RoHS Compliant

3. Application

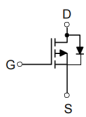
- Power Management in Telecom., Industrial Automation
- Motor Drives and Uninterruptible Power Supplies
- Current Switching in DC/DC&AC/DC(SR) Sub-systems

4. Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current (Note 1)	I_D	-13	A
Single Pulsed Avalanche Energy (Note 3)	E_{AS}	33	mJ
Thermal Resistance, steady-state	$R_{\theta JC}$	3.3	$^{\circ}\text{C}/\text{W}$
Power Dissipation	P_D	40	W
Junction Temperature	T_J	-55~+150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^{\circ}\text{C}$

Note: 1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating, pulse width limited by max. junction temperature.
3) E_{AS} condition : $T_J=25^{\circ}\text{C}$, $V_{DD}=-50\text{V}$, $V_{GS}=-10\text{V}$, $L=0.5\text{mH}$, $R_g=25\Omega$, $I_{AS}=-11.5\text{A}$.

5. Pinning information

Pin	Symbol	Description	Simplified outline	Equivalent Circuit	Marking	Package
1	G	Gate			MDD G10R160D XXY: Date code	TO-252
2	D	Drain				
3	S	Source				

6. $T_A=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-100	—	—	V
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$	—	—	± 100	nA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-100V, V_{GS}=0V$	—	—	-1	μA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.1	-1.5	-2.2	V
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=-10V, I_D=-12A$	—	145	170	m Ω
		$V_{GS}=-4.5V, I_D=-10A$	—	152	180	m Ω

7. Dynamic Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS}=0V$ $V_{DS}=-50V$ $f=1MHz$	—	2510	—	pF
C_{oss}	Output Capacitance		—	56	—	pF
C_{rss}	Reverse Transfer Capacitance		—	50	—	pF
Q_g	Total Gate Charge	$V_{GS}=-10V$ $V_{DS}=-50V$ $I_D=-10A$	—	17	—	nC
Q_{gs}	Gate Source Charge		—	4.5	—	nC
Q_{gd}	Gate Drain Charge		—	8	—	nC

8. Switching Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{d(on)}$	Turn on Delay Time	$V_{GS}=-10V$ $V_{DD}=-50V$ $I_D=-10A$ $R_G=9\Omega$	—	17	—	ns
t_r	Turn on Rise Time		—	16	—	ns
$t_{d(off)}$	Turn Off Delay Time		—	58	—	ns
t_f	Turn Off Fall Time		—	18	—	ns

9. Source Drain Diode Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{SD}	Drain-Source Diode Forward Voltage	$I_S=-13A, V_{GS}=0V$	—	-0.8	-1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-13A$ $di/dt=100A/\mu s$	—	33	—	ns
Q_{rr}	Body Diode Reverse Recovery Charge		—	49	—	nC

10. Electrical Characteristics Diagrams

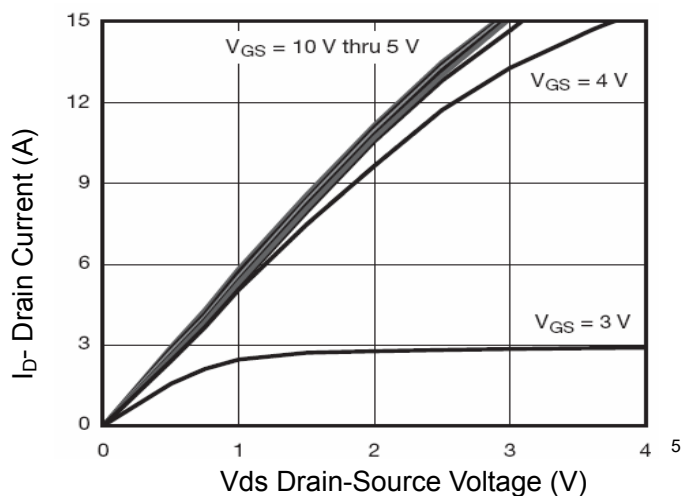


Figure 1. Typ. output characteristics

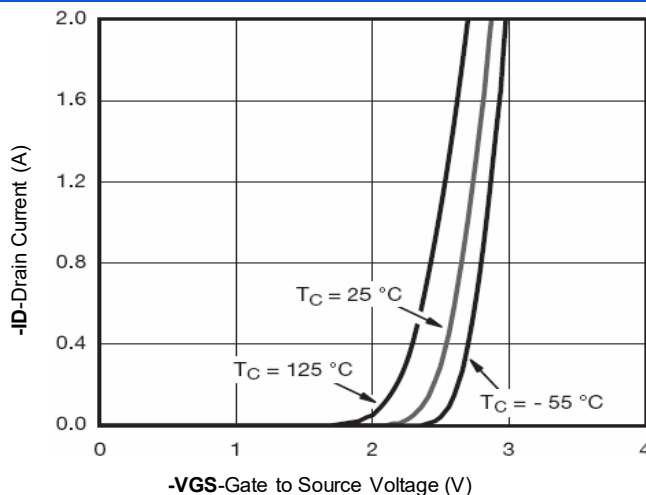


Figure 2. Typ. transfer characteristics

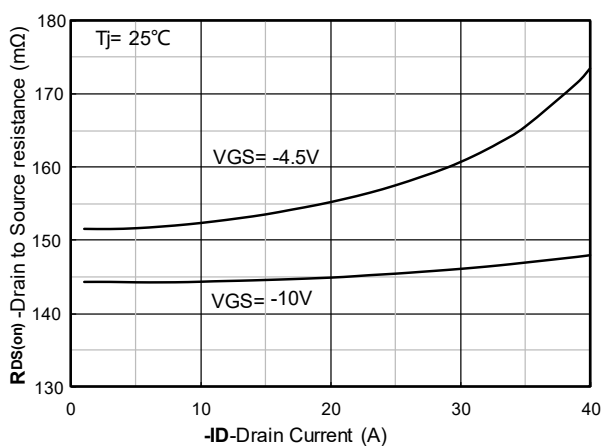


Figure 3. On-Resistance vs. Drain Current

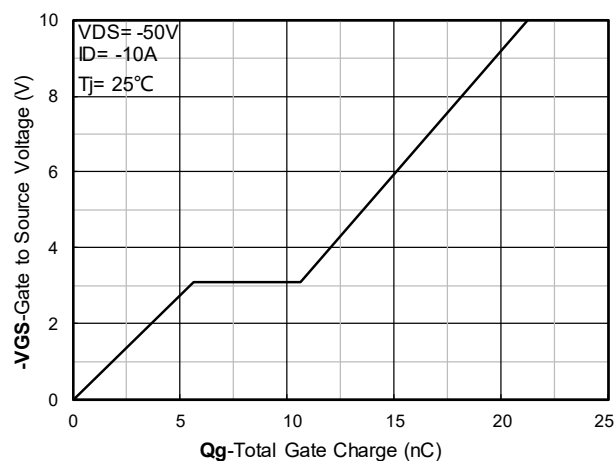


Figure 4. Gate Charge Characteristics

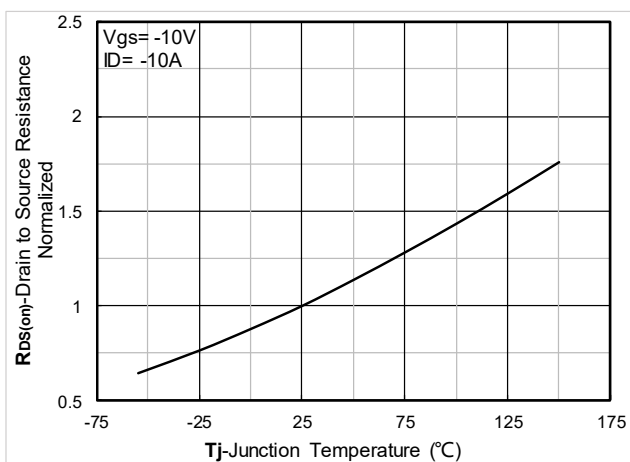


Figure 5. Normalized on Resistance vs. Junction Temperature

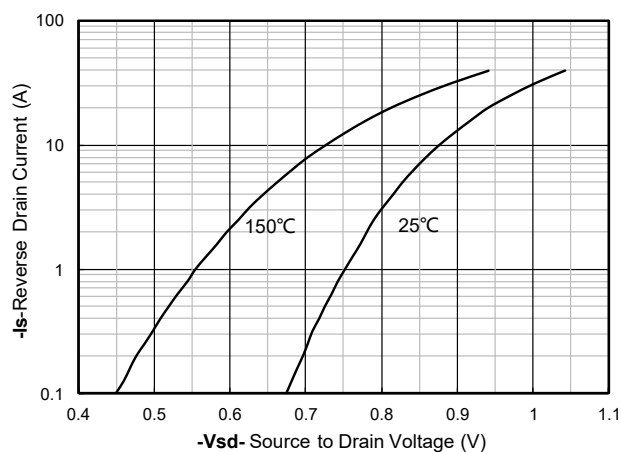
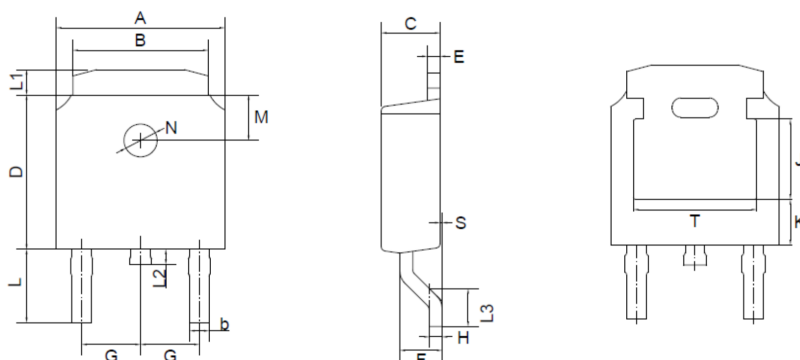


Figure 6. Forward characteristic of body diode

11. Outline Drawing

TO-252 Package Outline Dimensions



TO-252(D-PAK) mechanical data

UNIT		A	B	b	C	D	E	F	G	H	L	L1	L2	L3	S	M	N	J	K	T
mm	max	6.7	5.5	0.8	2.5	6.3	0.6	1.8	2.29	0.55	3.1	1.2	1.0	1.75	0.1	1.8	1.3	3.16	1.80	4.83
	min	6.3	5.1	0.3	2.1	5.9	0.4	1.3	TYPICAL	0.45	2.7	0.8	0.6	1.40	0.0	TYPICAL	TYPICAL	ref.	ref.	ref.
mil	max	264	217	31	98	248	24	71	90	22	122	47	39	69	4	71	51	124	71	190
	min	248	201	12	83	232	16	51	TYPICAL	18	106	31	24	55	0	TYPICAL	TYPICAL	ref.	ref.	ref.

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